

# Shengnan Zhu

## List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Time-Dependent Dielectric Breakdown of Commercial 1.2 kV 4H-SiC Power MOSFETs. IEEE Journal of the Electron Devices Society, 2021, 9, 633-639.	2.1	30
2	Gate Leakage Current and Time-Dependent Dielectric Breakdown Measurements of Commercial 1.2 kV 4H-SiC Power MOSFETs. , 2019, , .		14
3	Gate Oxide Reliability Studies of Commercial 1.2 kV 4H-SiC Power MOSFETs. , 2020, , .		12
4	The Road to a Robust and Affordable SiC Power MOSFET Technology. Energies, 2021, 14, 8283.	3.1	10
5	Threshold Voltage Instability of Commercial 1.2 kV SiC Power MOSFETs. , 2020, , .		8
6	Comparison of Gate Oxide Lifetime Predictions with Charge-to-Breakdown Approach and Constant-Voltage TDDB on SiC Power MOSFET. , 2021, , .		6
7	Impacts of Area-Dependent Defects on the Yield and Gate Oxide Reliability of SiC Power MOSFETs. , 2021, , .		1